

DPS-532-E/1.5~4mJ

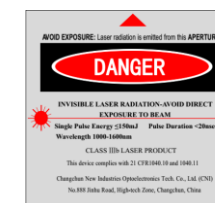
**HIGH ENERGY DIODE
PUMPED ALL-SOLID-STATE
Q-SWITCHED LASER**

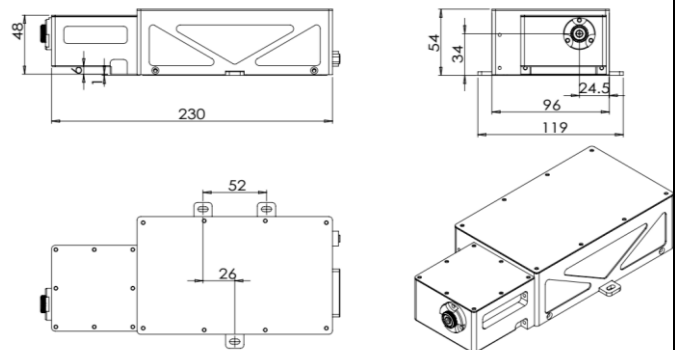
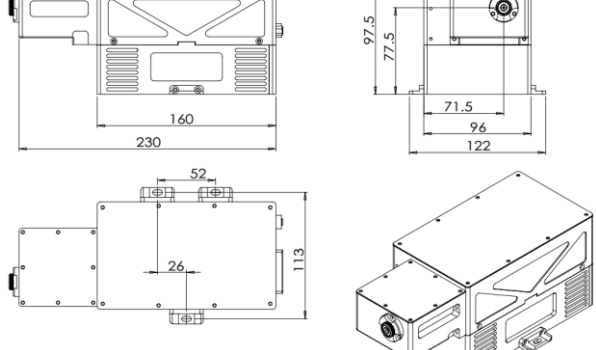
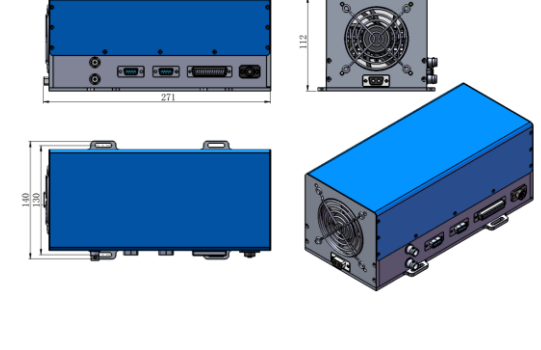
High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in LIBS, LIF, ICP-MS, LCD repair, scientific research, and so on.



SPECIFICATIONS

Wavelength (nm)	532±1	
Operating mode	Q-switched: EO (Electro-optic)	
Single pulse energy (mJ)	1.5	4
Pulse duration (ns)	<4	
Rep. rate (Hz)	1~50 (Optional), EXT	
Energy stability (rms)	<3%, <5%	
Beam divergence, full angle (mrad)	<3	
Beam diameter (mm)	~1	
Beam height from base plate (mm)	34	77.5
Warm-up time (minutes)	<15	
Cooled method	Conduction (DPS-532-E- I)	Air cooled (DPS-532-E- II)
Operating temperature (°C)	15~30	
Power supply (24V DC)	PSU-DPS-E	
Expected lifetime (pulses)	10 ⁹	
Warranty period	1 year	



DPS-532-E-I	DPS-532-E- II	PSU-DPS-E
 <p>230(L)×119(W)×54(H)mm³, 3kg Heat dissipation is offered by customer</p>	 <p>230(L)×122(W)×97.5(H)mm³, 3.5kg</p>	 <p>271 (L) ×140(W) ×112(H) mm³, 2.5 kg Rep. Rate and Current can be adjusted by touch screen</p>